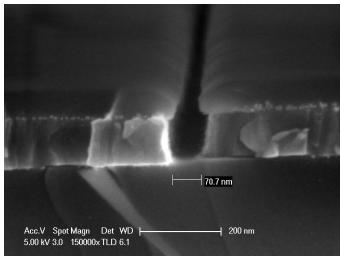
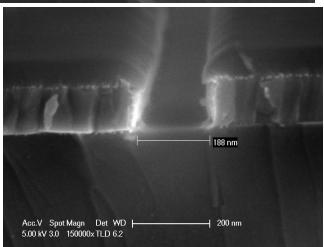


Cr Etch Recipe 1 – Smaller Undercut







Recipe for Cr-trench

- 24 sccm Cl2
- 6 sccm O2
- 1.33 Pa
- 600 W ICP, 50 W Bias
- Etch Rate: ~36nm/min.
- SiO2 hard Mask
- Small Undercut, sub-100nm features



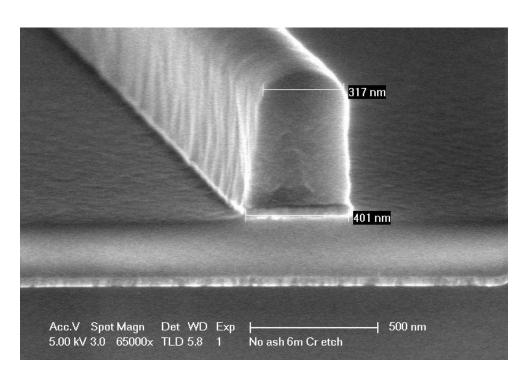
B. Mitchell





Cr Etch Process 2 – Lower Energy





G. Burek

PR Mask not removed

Recipe for Cr-mesa

- 26 sccm Cl2
- 4 sccm O2
- 1.0 Pa
- 400 W ICP, 15 W Bias
- Etch Rate: ~22 nm/min.
- PR Mask
- thick Cr-films (~100nm or thicker) can undercut



